

SEMICONDUCTOR DEVICE

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Abstract of JP63099558

PURPOSE:To achieve the implementation of a large scale system without decreasing reliability, by forming an insulating coating material using an insulating bonding agent in a space formed by an insulating substrate and a cap body so as to cover first wiring boards and a second wiring board.
CONSTITUTION:In a semiconductor device, an insulating bonding agent is filled so as to cover the main surface of a second wiring board 3, parts of first wiring boards 2 and parts of semiconductor chips, and the agent is hardened. Thus an insulating coating material 10 is formed. Because of the insulating property, electrodes 6a and 6b are not short-circuited, and electric functions are not impaired. The contact area between the first wiring boards 2 and the second wiring board 3 is increased. Strength between both wiring boards 2 and 3 becomes large owing to the adhesive property. A characteristic, which is resistant to mechanical shocks such as vibration, can be obtained. Even if the number of electrodes arranged between the first wiring boards 2 and the second wiring board 3 is increased, the mechanical connecting strength between the boards 2 and 3 is high, and reliability against mechanical shocks such as vibration is high. Therefore, the semiconductor device having a large scale system can be obtained.

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